TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SC4690

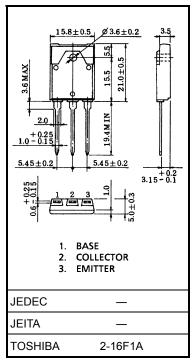
Power Amplifier Applications

Unit: mm

- High breakdown voltage: VCEO = 140 V (min)
- Complementary to 2SA1805
- Suitable for use in 70-W high fidelity audio amplifier's output stage

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	140	V	
Collector-emitter voltage		V _{CEO}	140	V	
Emitter-base voltage		V _{EBO}	5	V	
Collector current	DC	I _C	10	Α	
	Pulse	I _{CP}	20		
Base current		Ι _Β	1	А	
Collector power dissipation		P _C	80	W	
(Tc = 25°C)			80	VV	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



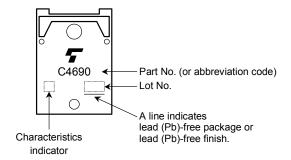
Weight: 5.8 g (typ.)

Electrical Characteristics (Tc = 25°C)

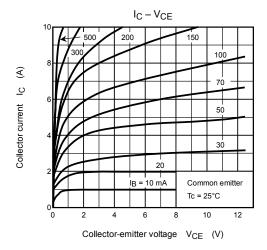
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 140 V, I _E = 0	_	_	5.0	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	5.0	μA
Collector-emitter breakdown voltage	V _{(BR) CEO}	$I_C = 50 \text{ mA}, I_B = 0$	140	_	_	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 5 V, I _C = 1 A	55		160	
	h _{FE (2)}	V _{CE} = 5 V, I _C = 5 A	35	85	_	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 7 A, I _B = 0.7 A	_	0.3	2.0	V
Base-emitter voltage	V_{BE}	V _{CE} = 5 V, I _C = 5 A	_	0.9	1.5	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 1 A	_	30	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	220	_	pF

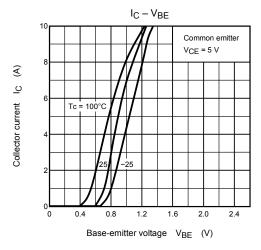
Note: $h_{FE(1)}$ classification R: 55 to 110, O: 80 to 160

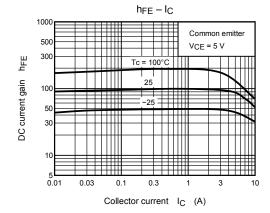
Marking

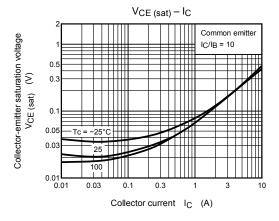


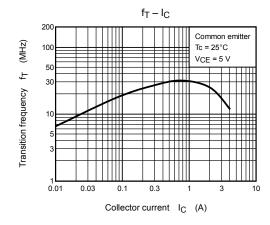
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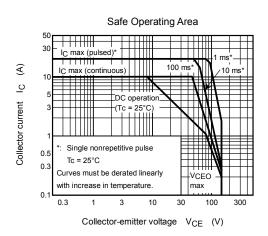












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